

Figure 1. Infrared absorbance change of inhibitors on SiO₂ through vapor phase method at a substrate temperature of 200 °C.

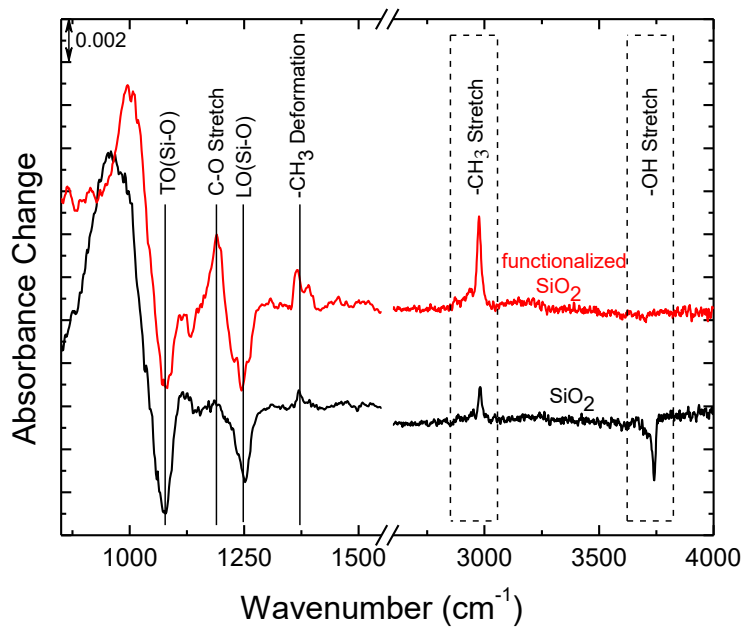


Figure 2. Infrared absorbance change during the reaction of ZTB with pristine SiO₂ and functionalized SiO₂ at a substrate temperature of 200 °C, respectively.